WPH4003-1E Datasheet

https://www.DiGi-Electronics.com

DiGi Electronics Part Number	WPH4003-1E-DG
Manufacturer	onsemi
Manufacturer Product Number	WPH4003-1E
Description	MOSFET N-CH 1700V 2.5A TO3PF
Detailed Description	N-Channel 1700 V 2.5A (Tc) 3W (Ta), 55W (Tc) Through Hole TO-3PF

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
WPH4003-1E	onsemi
Series:	Product Status:
-	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
1700 V	2.5A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
10V	10.5Ohm @ 1.5A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
-	48 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±30V	850 pF @ 30 V
FET Feature:	Power Dissipation (Max):
-	3W (Ta), 55W (Tc)
Operating Temperature:	Mounting Type:
150°C (TJ)	Through Hole
Supplier Device Package:	Package / Case:
TO-3PF	TO-3P-3 Full Pack
Base Product Number:	
WPH4003	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

Ordering number : ENA1967A

WPH4003

N-Channel Power MOSFET
1700V, 3A, 10.5Ω, TO-3PF-3L

ON Semiconductor®
http://onsemi.com

Features

- ON-resistance RDS (on) =8.2Ω (typ.)
- Input Capacitance Ciss=850pF (typ.)
- 10V drive

Specifications

Absolute Maximum Ratings at Ta=25°C

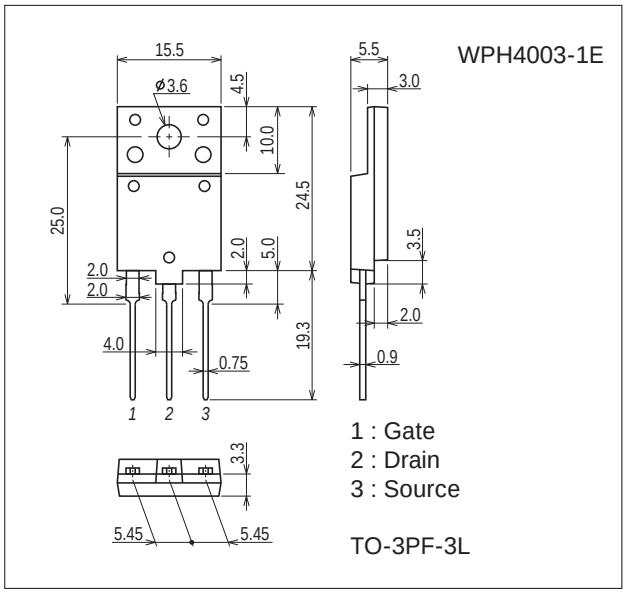
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		1700	V
Gate-to-Source Voltage	V_{GSS}		±30	V
Drain Current (DC)	I_{Dc}*1	Limited only maximum temperature Tch=150°C	3	A
	I_{Dpack}*2	Tc=25°C (Our ideal heat dissipation condition) *3	2.5	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	6	A
Allowable Power Dissipation	P_D		3.0	W
		Tc=25°C	55	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C
Avalanche Energy (Single Pulse) *4	E_{AS}		49	mJ
Avalanche Current *5	I_{AV}		3	A

Note :*1 Shows chip capability
*2 Package limited
*3 Our condition is radiation from backside.
The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.
*4 V_{DD}=50V, L=10mH, I_{AV}=3A (Fig.1)
*5 L≤10mH, single pulse

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

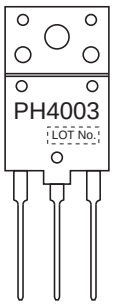
unit : mm (typ)
7538A-002



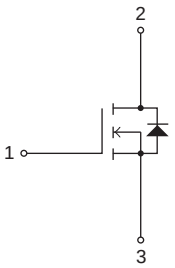
Product & Package Information

- Package : TO-3PF-3L
- JEITA, JEDEC : SC-96
- Minimum Packing Quantity : 30 pcs./magazine

Marking



Electrical Connection



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Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=10mA, V_{GS}=0V	1700			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=1360V, V_{GS}=0V			1	mA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±30V, V_{DS}=0V			±100	nA
Cutoff Voltage	V_{GS}(off)	V_{DS}=10V, I_D=1mA	2		4	V
Forward Transfer Admittance	| yfs |	V_{DS}=20V, I_D=1.5A	1.2	2.4		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)	I_D=1.5A, V_{GS}=10V		8.2	10.5	Ω
Input Capacitance	Ciss	V_{DS}=30V, f=1MHz		850		pF
Output Capacitance	Coss			90		pF
Reverse Transfer Capacitance	Crss			27		pF
Turn-ON Delay Time	t_d(on)	See Fig.2		19		ns
Rise Time	t_r			21		ns
Turn-OFF Delay Time	t_d(off)			200		ns
Fall Time	t_f			55		ns
Total Gate Charge	Qg	V_{DS}=200V, V_{GS}=10V, I_D=3A		48		nC
Gate-to-Source Charge	Qgs			6		nC
Gate-to-Drain “Miller” Charge	Qgd			22		nC
Diode Forward Voltage	V_{SD}	I_S=3A, V_{GS}=0V		0.8	1.5	V
Reverse Recovery Time	t_{rr}	See Fig.3		410		ns
Reverse Recovery Charge	Q_{rr}	I_S=3A, V_{GS}=0V, di/dt=100A/μs		3000		nC

Fig.1 Unclamped Inductive Switching Test Circuit

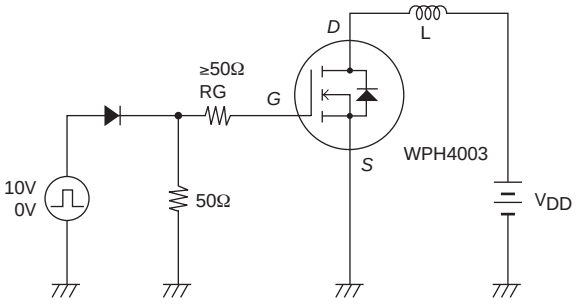


Fig.2 Switching Time Test Circuit

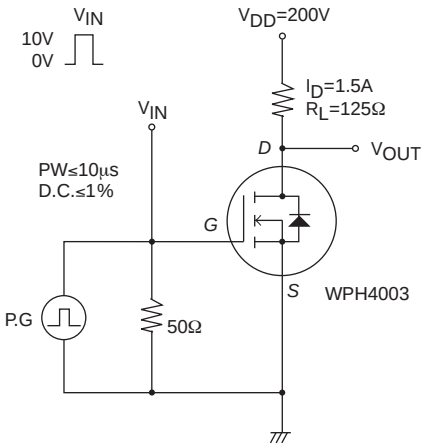
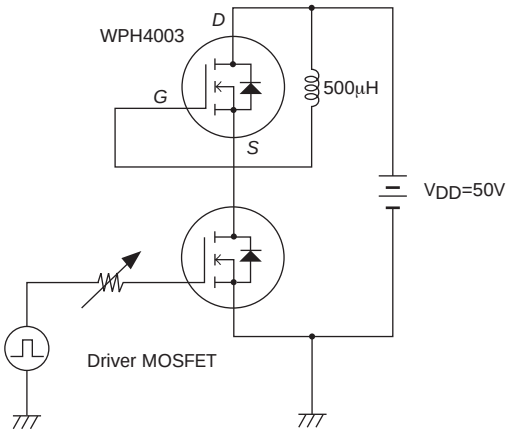


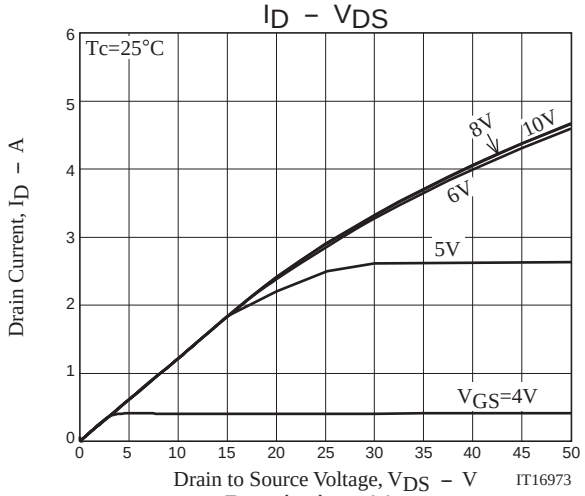
Fig.3 Reverse Recovery Time Test Circuit



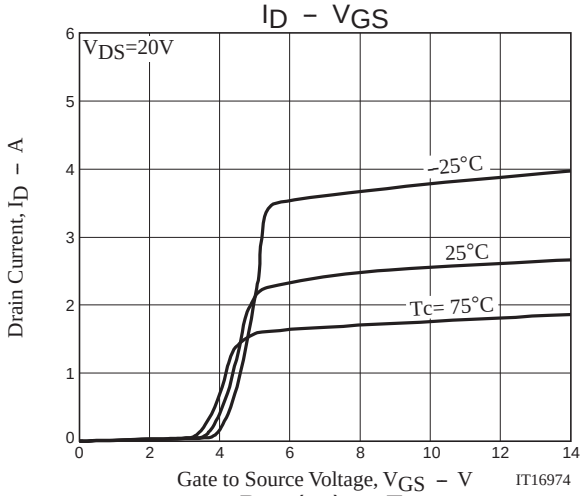
Ordering Information

Device	Package	Shipping	memo
WPH4003-1E	TO-3PF-3L	30pcs./magazine	Pb Free

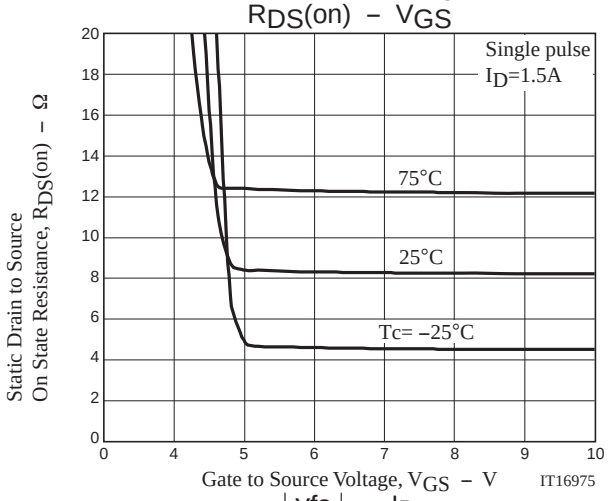
I_D – V_{DS}



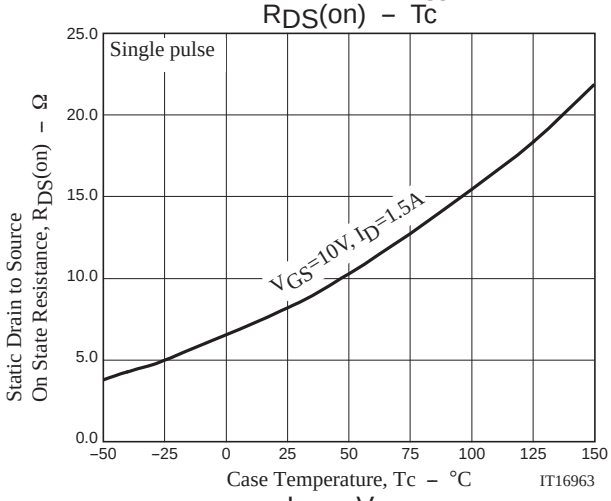
I_D – V_{GS}



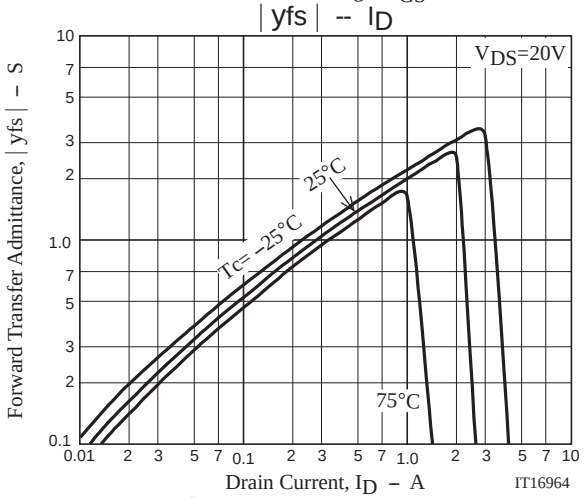
$R_{DS(on)}$ – V_{GS}



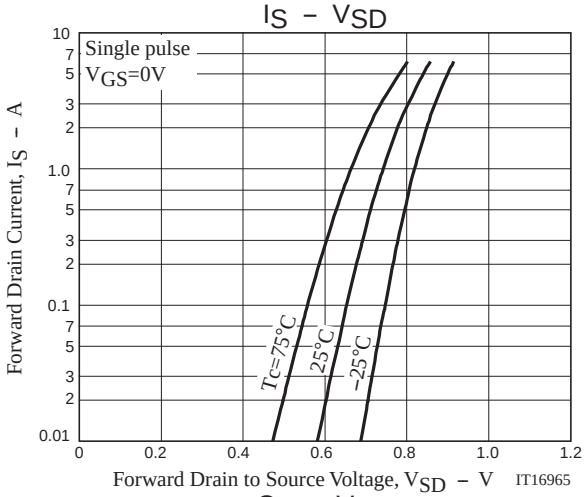
$R_{DS(on)}$ – Tc



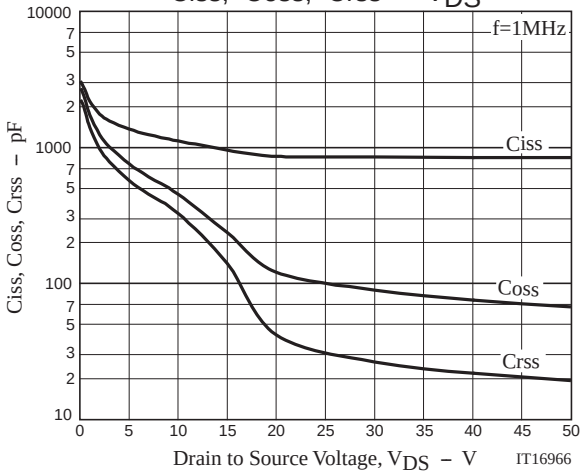
| yfs | -- I_D



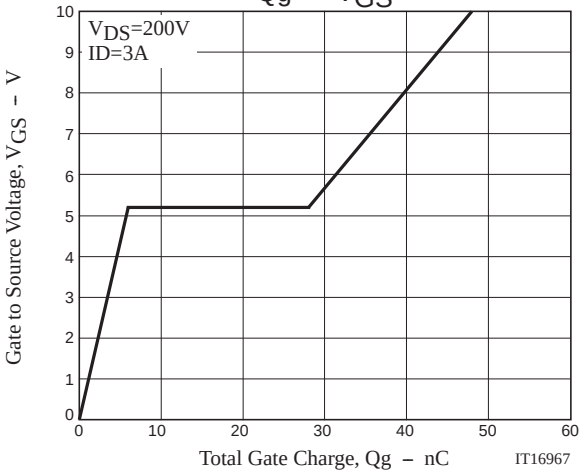
I_S – V_{SD}



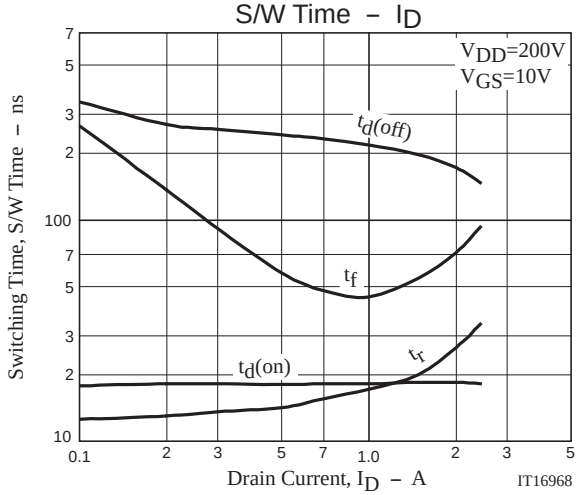
Ciss, Coss, Crss – V_{DS}



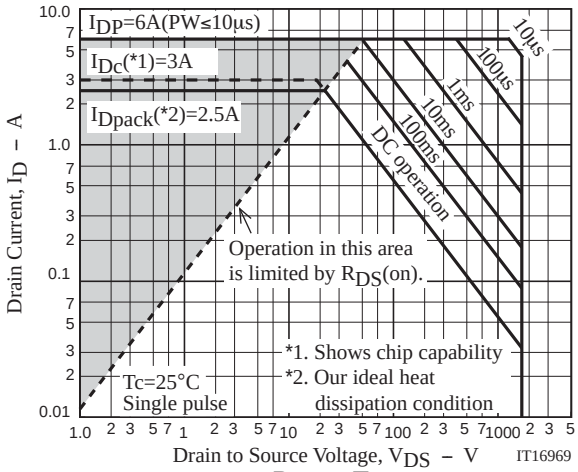
Qg – V_{GS}



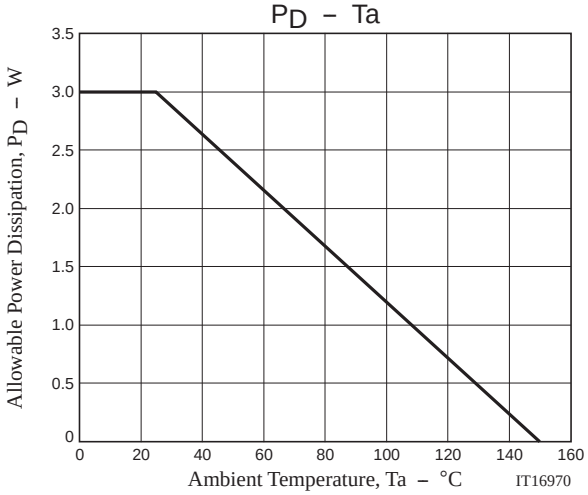
S/W Time – I_D



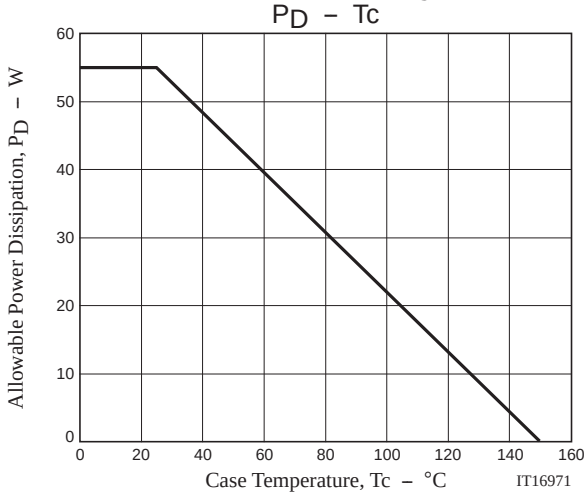
A S O



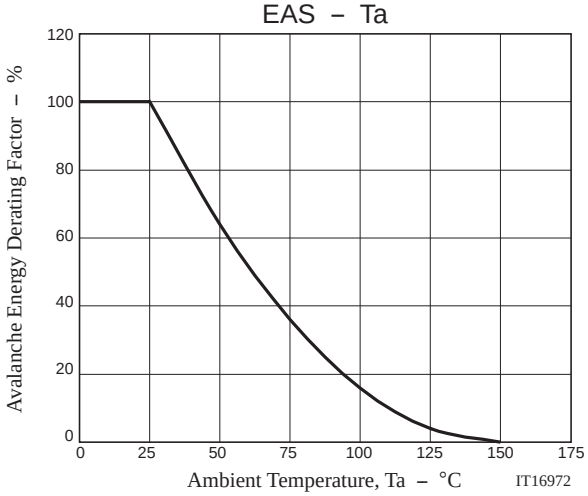
P_D – Ta



P_D – Tc



EAS – Ta



WPH4003

Magazine Specification

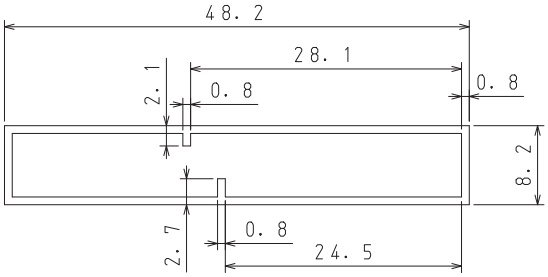
WPH4003-1E

1. Packing Format

Package Name	Maximum Number of devices contained (pcs)			Packing format	
	Magazine	Inner box	Outer box	Inner BOX	Outer BOX
TO-3PF-3L	30	360	1440	SPD-0V0001 12 magazines contained Dimensions:mm(external) 568×150×55	SPD-LV0010 4 inner boxes contained Dimensions:mm(external) 590x225x178

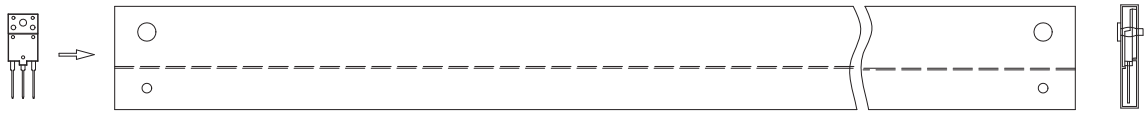
2. Magazine dimensions

(unit:mm)

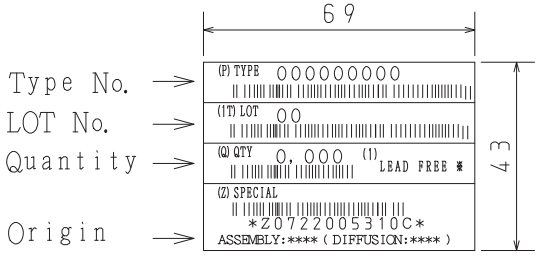


Tolerance=±0.2mm
Thickness=0.8±0.2mm
Length =508.0±1mm
Material =PVC or PET
(Antistatic treatment)

3. Storage method to magazine

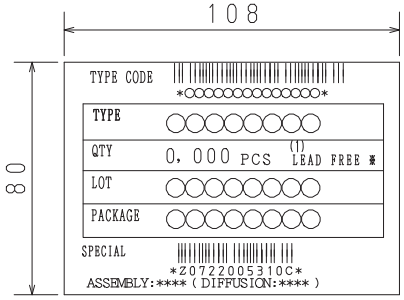


4. Inner box label (unit:mm)



5. Outer box label (unit:mm)

It is a label at the time of factory shipments.
The form of a label may change in physical distribution process.

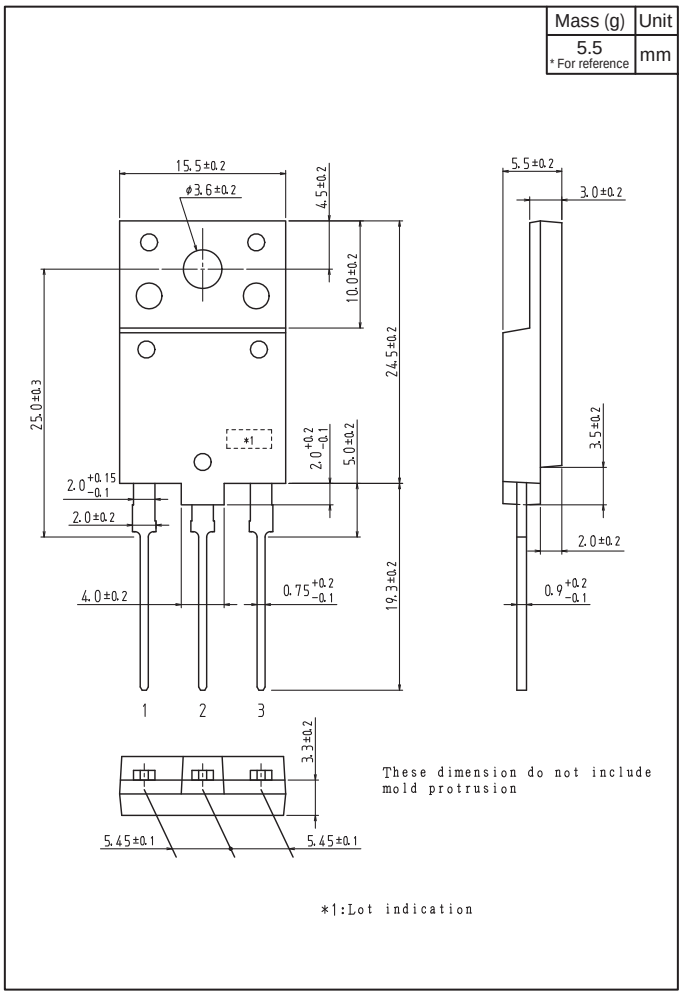


NOTE (1)
The LEAD FREE ※ description shows that the surface treatment of the terminal is lead free.

Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A

Outline Drawing

WPH4003-1E



Note on usage : Since the WPH4003 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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